

*SPECIFICATION AMENDMENTS*

Replace the paragraph beginning at page 13, line 15 with:

Fig. 10 is a cross-sectional view taken along line ~~A-A'~~ X-X of Fig. 9;

Replace the paragraph beginning at page 13, line 18 with:

Fig. 12 is a cross-sectional view taken along line ~~A-A'~~ XII-XII of the MOS transistor shown in Fig. 11;

Replace the paragraph beginning at page 13, line 20 with:

Fig. 13 is a cross-sectional view taken along line ~~B-B'~~ XIII-XIII of the MOS transistor shown in Fig. 11;

Replace the paragraph beginning at page 26, line 15 with:

Fig. 9 is a top pattern diagram illustrating the configuration of a MOS transistor according to a fifth embodiment of the present invention. Fig. 10 is a cross-sectional view taken along line ~~A-A'~~ X-X shown in Fig. 9. The fifth embodiment explains still another configuration example of the MOS transistor in which the control gates are provided located on ~~both the~~ opposite sides of the main gate, in the ~~gate~~ lengthwise direction of the gate, namely, on the ~~sides of the~~ source area and the drain area sides in the MOS transistor shown in Fig. 1B.

Replace the paragraph beginning at page 28, line 16 with:

Figs. 11 to 13 are pattern diagrams illustrating the configuration of a MOS transistor according to a sixth embodiment of the present invention. Fig. 11 is a top view. Fig. 12 is a cross-sectional view taken along line ~~A-A'~~ XII-XII of Fig. 11. Fig. 13 is a cross-sectional view taken along line ~~B-B'~~ XIII-XIII of Fig. 11.